High-temperature 60 V, 3 A Schottky barrier rectifier 15 October 2012

**Product data sheet** 

#### **Product profile** 1.

### 1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a SOD128 small and flat lead Surface-Mounted Device (SMD) plastic package.

### 1.2 Features and benefits

- Average forward current:  $I_{F(AV)} \le 3 A$ •
- Reverse voltage:  $V_R \le 60 V$ •
- Low forward voltage
- . High power capability due to clip-bonding technology
- Small and flat lead SMD plastic package
- AEC-Q101 qualified •
- High temperature T<sub>i</sub> ≤ 175 °C

### 1.3 Applications

- Low voltage rectification •
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Reverse polarity protection

### 1.4 Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I <sub>F</sub>	forward current	T <sub>sp</sub> = 160 °C		-	-	4.2	А
$I_{F(AV)}$	average forward current	δ = 0.5 ; f = 20 kHz; T <sub>amb</sub> ≤ 80 °C; square wave	[1]	-	-	3	А
		$\delta$ = 0.5 ; f = 20 kHz; T <sub>sp</sub> ≤ 165 °C; square wave		-	-	3	А
V <sub>R</sub>	reverse voltage	T <sub>j</sub> = 25 °C		-	-	60	V
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 3 A; T <sub>j</sub> = 25 °C		-	460	530	mV
I <sub>R</sub>	reverse current	$\label{eq:transform} \begin{array}{l} T_{j} = 25 \ ^{\circ}\text{C}; \ V_{\text{R}} = 60 \ \text{V}; \ t_{p} \leq 300 \ \mu\text{s}; \\ \delta \leq 0.02 \ ; \ \text{pulsed} \end{array}$		-	80	200	μA







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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t <sub>rr</sub>	reverse recovery time	$I_R = 0.5 \text{ A}; I_F = 0.5 \text{ A}; I_{R(meas)} = 0.1 \text{ A};$	-	12	-	ns
		T <sub>j</sub> = 25 °C				

[1] Device mounted on a ceramic Printed-Circuit Board (PCB), Al<sub>2</sub>O<sub>3</sub>, standard footprint.

### 2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	К	cathode[1]		1 🛃 2
2	А	anode		sym001
			SOD128	

[1] The marking bar indicates the cathode.

### 3. Ordering information

Table 3. Ordering information				
Type number	Package			
	Name	Description	Version	
PMEG6030ETP	SOD128	plastic surface-mounted package; 2 leads	SOD128	

### 4. Marking

Table 4. Marking codes	
Type number	Marking code
PMEG6030ETP	DA

# 5. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>R</sub>	reverse voltage	T <sub>j</sub> = 25 °C		-	60	V
I <sub>F</sub>	forward current	T <sub>sp</sub> = 160 °C		-	4.2	А
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5 ; f = 20 kHz; T <sub>amb</sub> ≤ 80 °C; square wave	[1]	-	3	A
		$\delta$ = 0.5 ; f = 20 kHz; T <sub>sp</sub> ≤ 165 °C; square wave		-	3	A
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 8 ms; $T_{j(init)}$ = 25 °C; square wave		-	50	A
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Symbol	Parameter	Conditions		Min	Max	Unit
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[2]	-	750	mW
		[3]	-	1250	mW	
		[1]	-	2500	mW	
Т <sub>ј</sub>	junction temperature			-	175	°C
T <sub>amb</sub>	ambient temperature			-55	175	°C
T <sub>stg</sub>	storage temperature			-65	175	°C

[1] Device mounted on a ceramic Printed-Circuit Board (PCB), Al<sub>2</sub>O<sub>3</sub>, standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

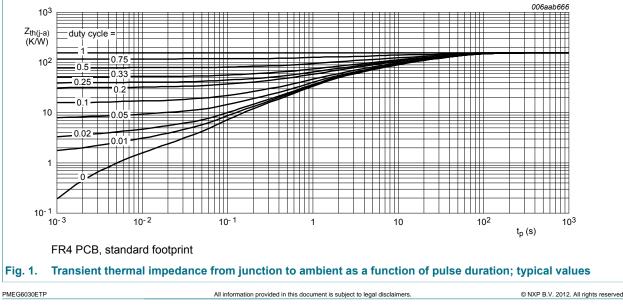
[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.

### 6. Thermal characteristics

Table 6. Thermal characteristics							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
ui(j-u)	thermal resistance	-	[1][2]	-	-	200	K/W
	from junction to		[1][3]	-	-	120	K/W
	ampient		[1][4]	-	-	60	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		[5]	-	-	12	K/W

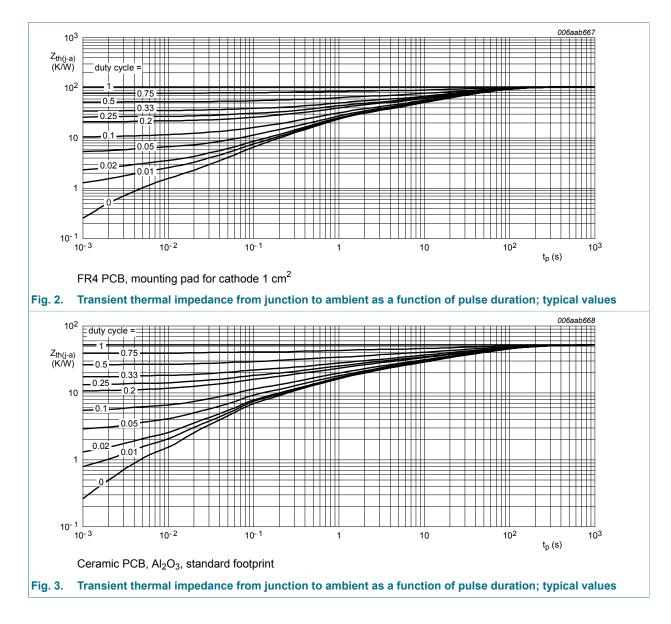
[1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P<sub>R</sub> are a significant part of the total power losses.

- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.
- [4] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.
- [5] Soldering point of cathode tab.



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# 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>F</sub> forward voltage	I <sub>F</sub> = 0.1 A; T <sub>j</sub> = 25 °C	-	290	330	mV	
		I <sub>F</sub> = 0.5 A; T <sub>j</sub> = 25 °C	-	340	400	mV
		I <sub>F</sub> = 1 A; T <sub>j</sub> = 25 °C	-	380	440	mV
		I <sub>F</sub> = 1.5 A; T <sub>j</sub> = 25 °C	-	400	470	mV
		I <sub>F</sub> = 2 A; T <sub>j</sub> = 25 °C	-	430	500	mV
		I <sub>F</sub> = 3 A; T <sub>j</sub> = 25 °C	-	460	530	mV

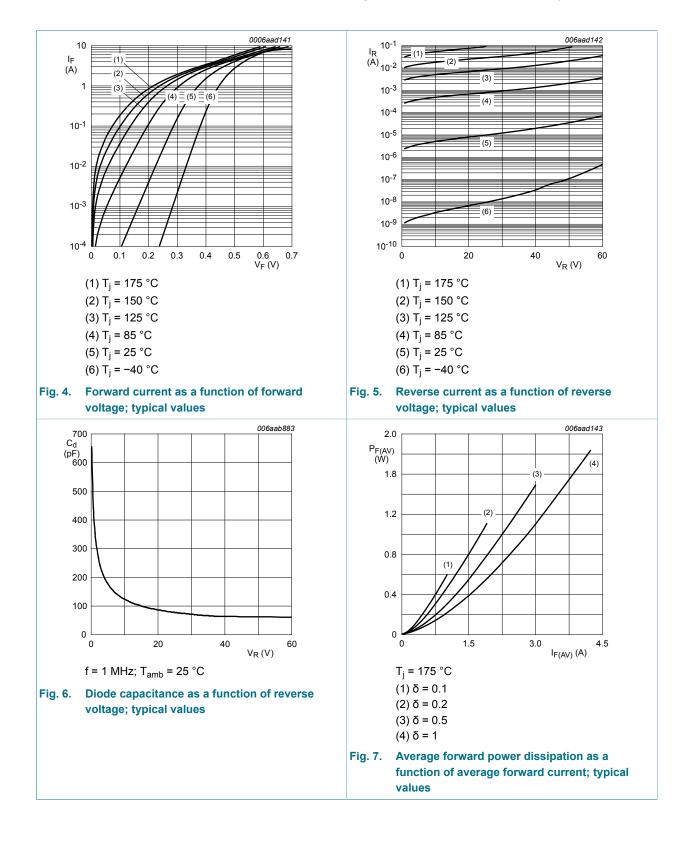
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		I <sub>F</sub> = 3 A; T <sub>j</sub> = -40 °C	-	510	590	mV
		I <sub>F</sub> = 3 A; T <sub>j</sub> = 125 °C	-	405	480	mV
	I <sub>F</sub> = 3 A; T <sub>j</sub> = 150 °C	-	390	460	mV	
	I <sub>F</sub> = 3 A; T <sub>j</sub> = 175 °C	-	370	450	mV	
I <sub>R</sub> reverse current	reverse current	$V_R$ = 5 V; T <sub>j</sub> = 25 °C; t <sub>p</sub> ≤ 300 µs; $\delta \le 0.02$ ; pulsed	-	4	-	μA
		$V_R$ = 10 V; T <sub>j</sub> = 25 °C; t <sub>p</sub> ≤ 300 µs; $\delta$ ≤ 0.02 ; pulsed	-	5	-	μA
		$V_R$ = 60 V; T <sub>j</sub> = 25 °C; t <sub>p</sub> ≤ 300 µs; $\delta \le 0.02$ ; pulsed	-	80	200	μA
		$V_R$ = 60 V; T <sub>j</sub> = -40 °C; t <sub>p</sub> ≤ 300 µs; $\delta \le 0.02$ ; pulsed	-	0.5	10	μA
		$V_R$ = 60 V; T <sub>j</sub> = 125 °C; t <sub>p</sub> ≤ 300 µs; $\delta \le 0.02$ ; pulsed	-	45	150	mA
C <sub>d</sub>	diode capacitance	V <sub>R</sub> = 1 V; f = 1 MHz; T <sub>j</sub> = 25 °C	-	360	-	pF
		V <sub>R</sub> = 10 V; f = 1 MHz; T <sub>j</sub> = 25 °C	-	120	-	pF
t <sub>rr</sub>	reverse recovery time	$I_{F} = 0.5 \text{ A}; I_{R} = 0.5 \text{ A}; I_{R(meas)} = 0.1 \text{ A};$ $T_{j} = 25 \text{ °C}$	-	12	-	ns
V <sub>FRM</sub>	peak forward recovery voltage	$I_F = 1 \text{ A}; \text{ d}_F/\text{d}t = 40 \text{ A}/\mu\text{s}; \text{ T}_j = 25 ^\circ\text{C}$	-	425	-	mV

#### High-temperature 60 V, 3 A Schottky barrier rectifier

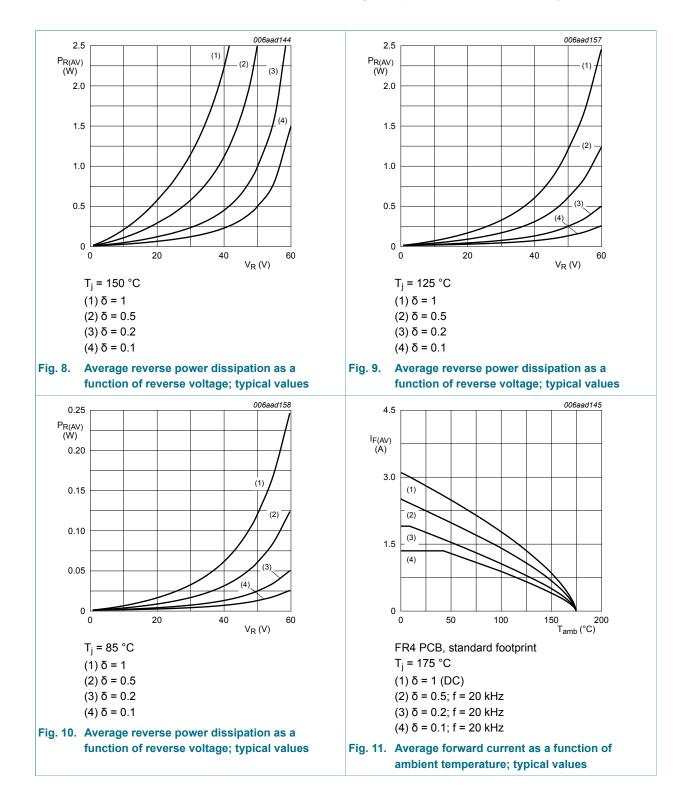


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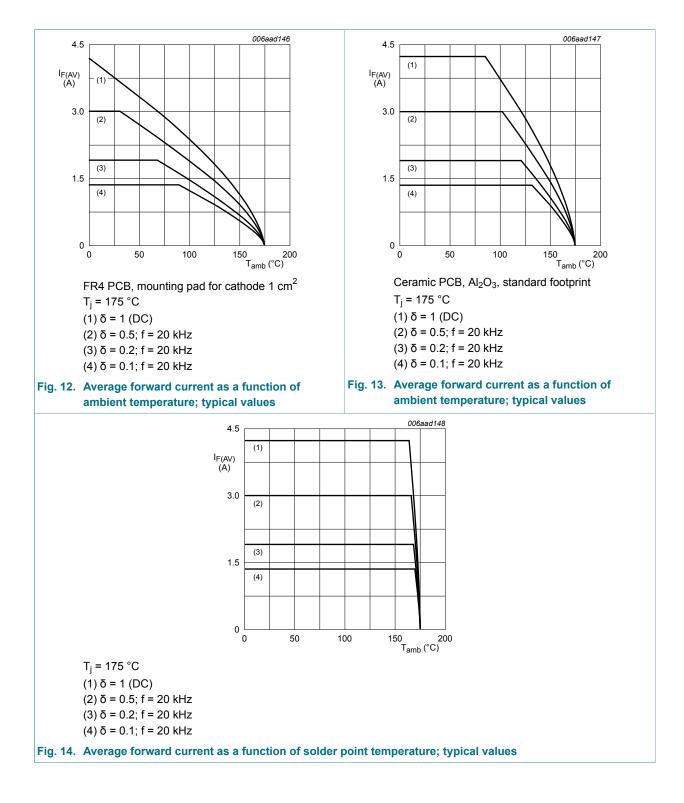


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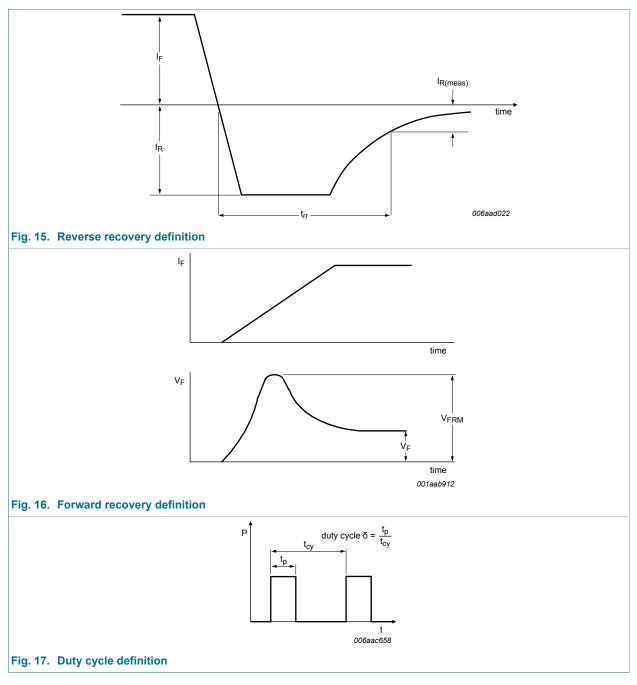


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#### Test information 8.



The current ratings for the typical waveforms are calculated according to the equations:  $I_{F(AV)} = I_M \times \delta$  with  $I_M$  defined as peak current,  $I_{RMS} = I_{F(AV)}$  at DC, and  $I_{RMS} = I_M \times \sqrt{\delta}$  with I<sub>RMS</sub> defined as RMS current.

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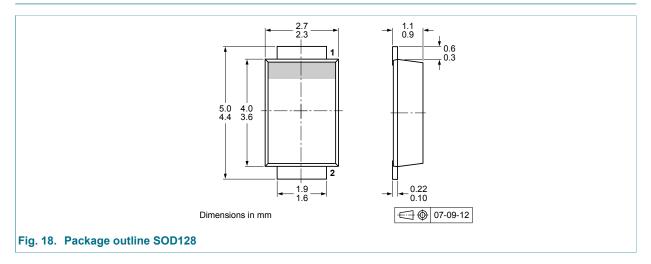
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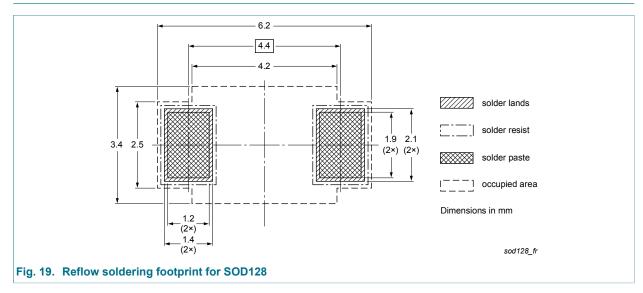
#### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

# 9. Package outline



# 10. Soldering



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## 11. PMEG6030ETP

Table 8. Revision his	Ible 8. Revision history					
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PMEG6030ETP v.1	20121015	Product data sheet	-	-		

#### High-temperature 60 V, 3 A Schottky barrier rectifier

### 12. Legal information

#### 12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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